

AMENDMENTS TO THE SPECIFICATION

1. Please substitute paragraph [0015] in "BRIEF DESCRIPTION OF THE DRAWINGS" section of the specification with the following amended paragraph:

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"Fig.1 to Fig.[10]2 are schematic cross-sectional diagrams showing the process for making a bottled shaped trench for DRAM devices according to one preferred embodiment of this invention."

10 2. Please substitute paragraph [0016] as follows:

"Please refer to Fig.1 to Fig.[10]2. Fig.1 to Fig.[10]2 are schematic cross-sectional diagrams showing the process for making a bottled shaped trench for DRAM devices according to one preferred embodiment of this invention. As shown in
15 Fig.1, a semiconductor substrate 10 such as a silicon substrate is provided. The semiconductor substrate 10 has a main surface 11, on which various semiconductor devices such as transistors are formed in later stages. A pad oxide layer 12 and a pad nitride layer 14 are sequentially formed on the main surface 11 of the semiconductor substrate 10 by any methods known in the art, for example, thermal growth or
20 chemical vapor deposition (CVD). Preferably, the pad oxide layer 12 has a thickness of about 50 angstroms, more preferably, less than 50 angstroms."